Plasma-Enhanced ALD of TiN: Effect of the N-Source on the Growth and Quality of the Thin Films

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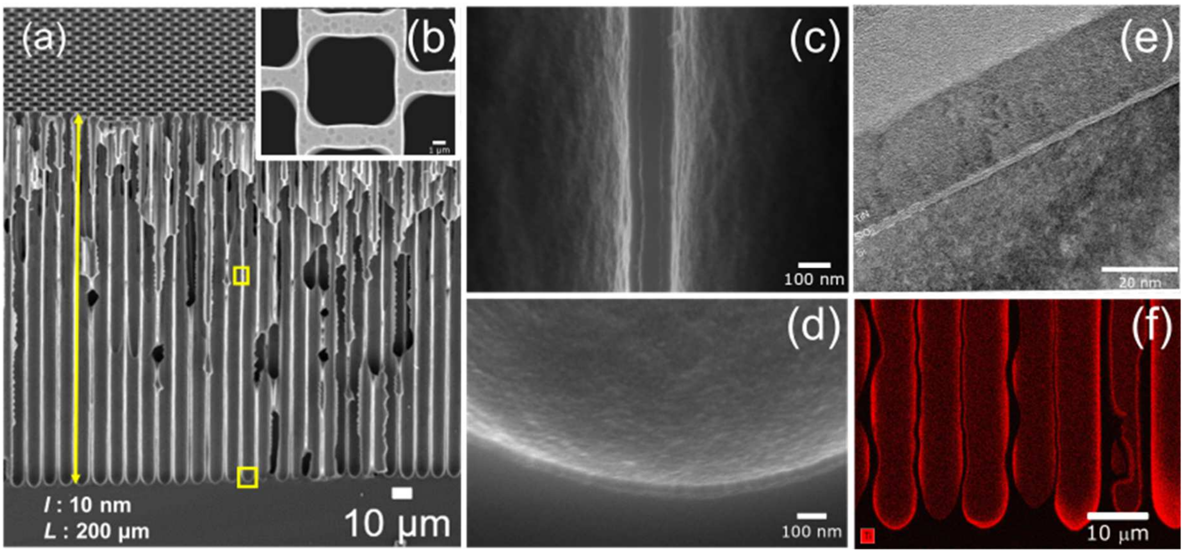

Figure 1 : TiN thin film with plasma NH_3, (a-d) SEM cross-section on a macroporous Si substrate (a) and top view (b), middle (c) and bottom of a pore (rectangles in (a)), TEM image of a deposit on planar Si (e) and EDX mapping with Ti in red (f).